

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

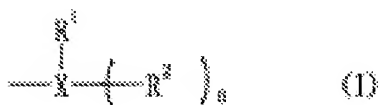
1. (currently amended) A material for chemical vapor deposition comprising a precursor composed of a metal compound, wherein the material contains 100 or less particles having a size of 0.5  $\mu\text{m}$  or more in 1 ml, in particle measurement by a light scattering ~~type~~ submerged particle detector in a liquid phase.

2. (currently amended) The material for chemical vapor deposition according to claim 1, wherein the number of particles having a size of 0.3  $\mu\text{m}$  or more is 100 or less in 1 ml, in particle measurement by a light scattering ~~type~~ submerged particle detector.

3. (currently amended) The material for chemical vapor deposition according to claim 1, wherein the number of particles having a size of 0.2  $\mu\text{m}$  or more is 1000 or less in 1 ml, in particle measurement by a light scattering ~~type~~ submerged particle detector.

4. (currently amended) The material for chemical vapor deposition according to claim 3, wherein the number of particles having a size of 0.2  $\mu\text{m}$  or more is 100 or less in 1 ml, in particle measurement by a light scattering ~~type~~ submerged particle detector.

5. (previously presented) The material for chemical vapor deposition according to claim 1, wherein the precursor is composed of a metal compound having a structure wherein the group represented by general formula (I) shown below bonds to the metal atom:



wherein X represents an oxygen atom or a nitrogen atom; n represents 0 when X is an oxygen atom or n represents 1 when X is a nitrogen atom;  $\text{R}^1$  represents an organic group having 1 to 10 carbon atoms; and  $\text{R}^2$  represents a hydrogen atom or an organic group having 1 to 10 carbon atoms.

6. (previously presented) The material for chemical vapor deposition according to claim 1, wherein the precursor is composed of a metal compound having a structure wherein the group represented by general formula (II) shown below bonds to the metal atom:



wherein R<sup>3</sup> represents an alkyl group having 1 to 8 carbon atoms or a cyclopentadienyl group having 1 to 10 carbon atoms.

7. (previously presented) The material for chemical vapor deposition according to claim 1, wherein the metal compound is selected from an aluminum compound, a titanium compound, a zirconium compound, a hafnium compound, a tantalum compound, and a niobium compound.

8. (original) The material for chemical vapor deposition according to claim 7, wherein the metal compound is a hafnium compound.

9. (previously presented) The material for chemical vapor deposition according to claim 1, which is delivered or fed in a liquid phase.

10. (canceled)

11. (currently amended) The material for chemical vapor deposition according to claim 2, wherein the number of particles having a size of 0.2  $\mu\text{m}$  or more is 1000 or less in 1 ml, in particle measurement by a light scattering ~~type~~ submerged particle detector.